FREE-p: Protecting Non-Volatile Memory against both Hard and Soft Errors

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Challenge in emerging non-volatile memory

- Finite write endurance
- PCRAM cells wear out after 10⁸ writes on average
 - Actual advertised specification is only 10⁶
- Process variation exacerbates the problem
 - Some cells fail earlier than others

Limitations of Prior solutions

- Tolerate only hard cell errors
 - Can't cover soft cell errors, errors on the periphery, wires, package, ...
- Require custom logic within NVRAM devices





Fine-grained Remapping with ECC and Embedded-pointer

- Multi-tiered ECC with fast and slow paths
- Fine-grained remapping
 - Re-use a "dead" 64B block for storing a remap pointer
 - Architectural techniques to accelerate address remapping
- Detection/correction at the memory controller
 - Allow simple NVRAM devices
 - Tolerate hard/soft errors in the cell array, periphery, wire, ...
- Trade off performance at the end of life with storage device cost and complexity
 - Near-zero performance penalty initially
 - Less than 2% penalty, even at 7 years
- Up to 26% longer lifetime





Prior Solutions and Their Limitations





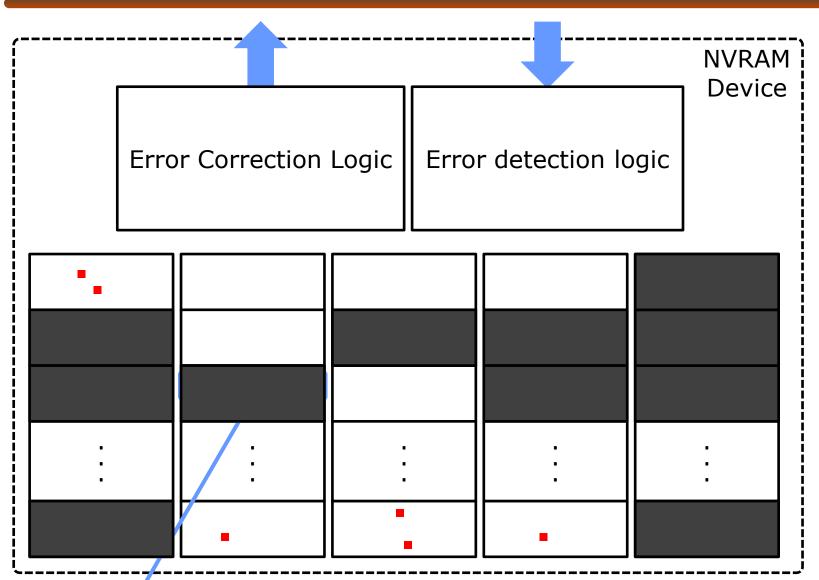
Prior solutions

- Avoiding unnecessary writes
- Wear-leveling
 - Widely used in FLASH memory
- Tolerating wear-out failures
 - Built-in hard bit-error correcting mechanisms
 - Coarse-grained remapping
 - DRM: Dynamically Replicating Memory
 - ECP: Error Correcting Pointer
 - SAFER: Stuck-At-Failure Error Recovery





Prior Work: Tolerating Wear-out Failures





Limitations of Prior Work

Only HARD cell errors

- Can't detect/correct SOFT errors
 - Resistance drift in PCRAM
- Can't detect/correct errors on periphery, wires, and packaging
- Supporting chipkill-correct?

Error detection/correction logic within NVRAM devices

- Memory industry favors SIMPLE and CHEAP devices
- Error detection/correction in DRAM
 - DRAM chips only store data
 - Additional DRAM chips for storing redundant information
 - Error detection/correction is done at the memory controller
- Better follow the same design strategy in NVRAM systems





FREE-p



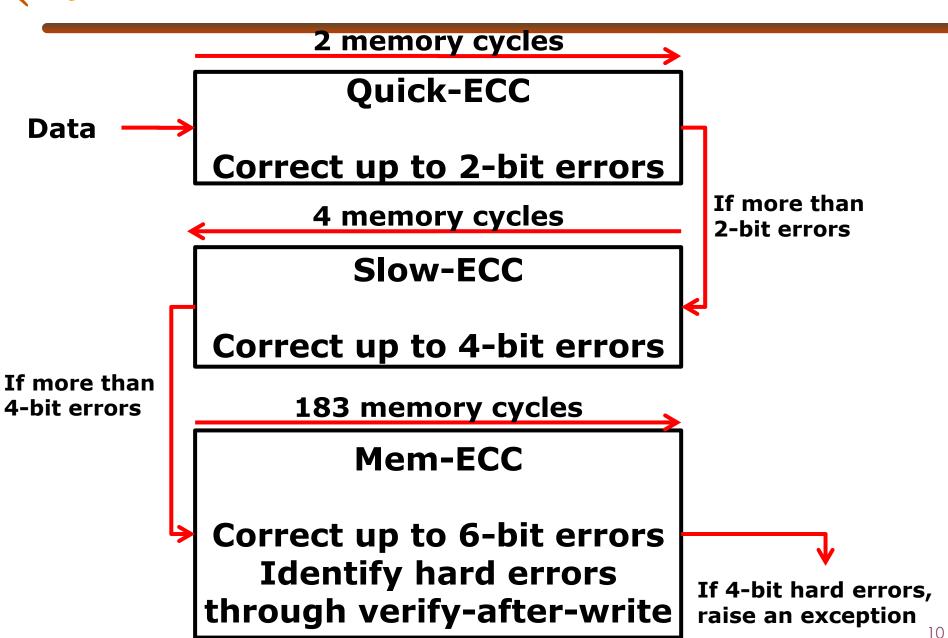


Multi-tiered ECC

- 6EC-7ED BCH code
 - 6-bit error correcting 7-bit error detecting
 - 61 bits for 64B data (less than 12.5% overhead)
- Tolerate up to 4 bit wear-out failures and 2 bit soft errors
- Low-latency decoding for common case operations
 - Quick-, Slow-, and Mem-ECC
 - Extend two-tiered decoding of Hi-ECC [Wilkerson ISCA'10]
 - Fast-path quick-ECC for most initial period



Multi-tiered ECC (Cont'd)



Dealing with Intolerable Failures

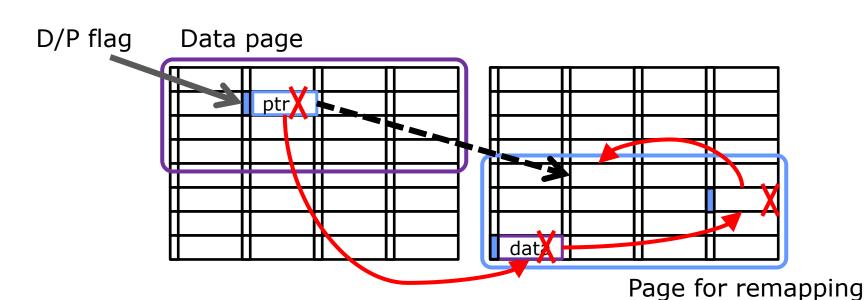
- Eventually, some blocks become faulty
 - More than 4 wear-out failures per block
- Coarse-grained remapping (prior solutions)
 - Leverage virtual-to-physical mapping
 - Mapping unit: 4kB or larger
 - A block with intolerable failure maps out the whole page
- Fine-grained remapping
 - Disable only a faulty block
 - Mapping unit: 64B
 - Effectively handle both random and concentrated errors





Fine-grained Remapping (FR) with Embedded-pointer

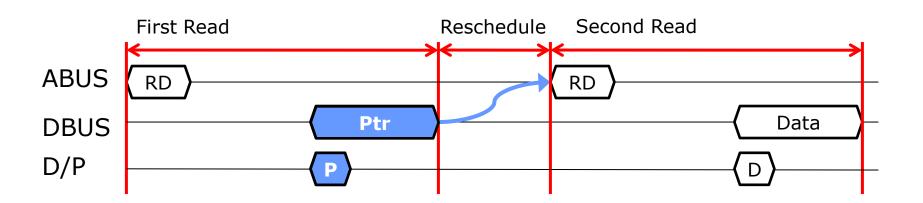
- Embed a 64-bit pointer within a faulty block
 - There are still-functional bits in a faulty block
 - Use 7-Modular Redundancy to tolerate the failures
- 1-bit D/P flag per 64B block
 - Identify a block is remapped or not
- Avoid chained remapping
 - Embed always the FINAL pointer





Read with FR

- Read data and D/P flag
- If a data block is remapped
 - Read the remapped block
 - Increase read latency, waste bandwidth
 - Penalty increases as NVRAM wear out





How to Mitigate This Penalty?

Remap pointer cache

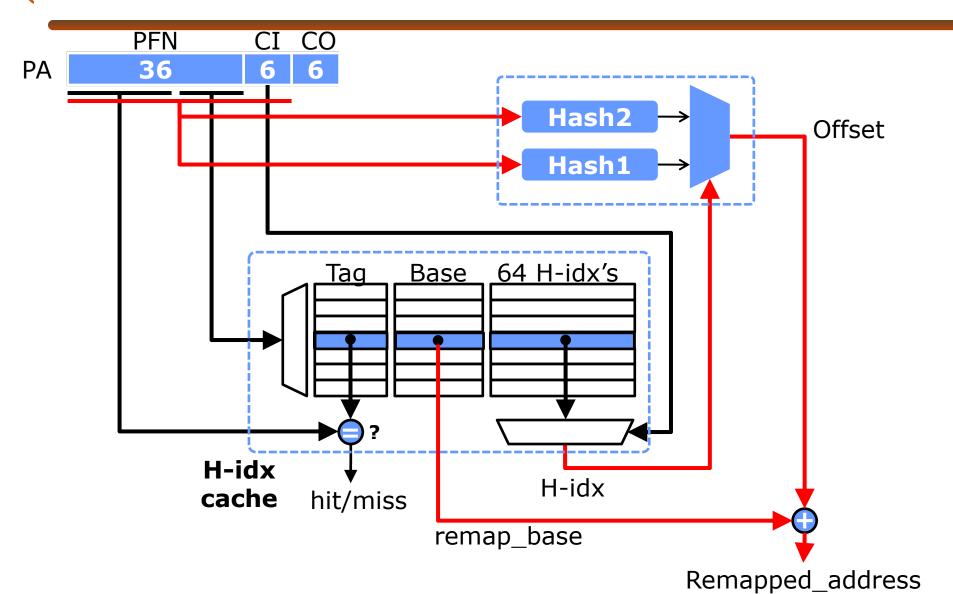
- Cache remap pointers
- Avoid reading remap pointer from NVRAM when cache hit

Hash based index cache

- Pre-defined hash functions for remapping
 - Compute, not cache, remap pointer
- H-idx: which hash function is used for remapping?
 - 0: not remapped
 - 1 or 2: remapped using one of the hash functions
 - 3: hash collision
 - All candidate locations are already used for other blocks
 - Need to read the remap pointer
 - 2 bits per 64B block



Hash-Based Index Cache



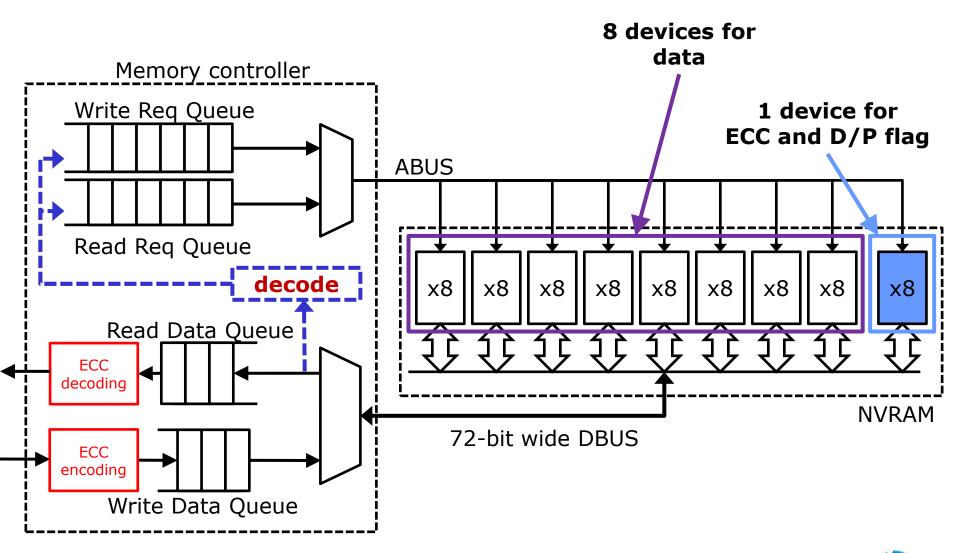


Index Cache (Cont'd)

- Fill/evict with TLB
 - 100% read hit rate
- Read remap pointers only when
 - Dirty write-back misses the index cache (rare)
 - Hash collision (rare with good hash functions)
- OS should be aware of hash functions



Memory System Organization with FREE-p



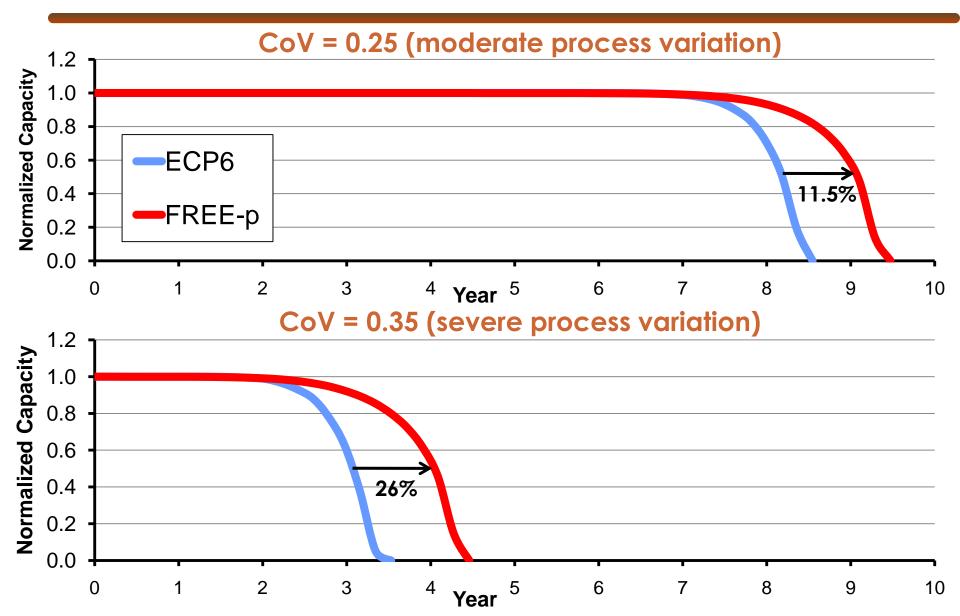


Evaluation



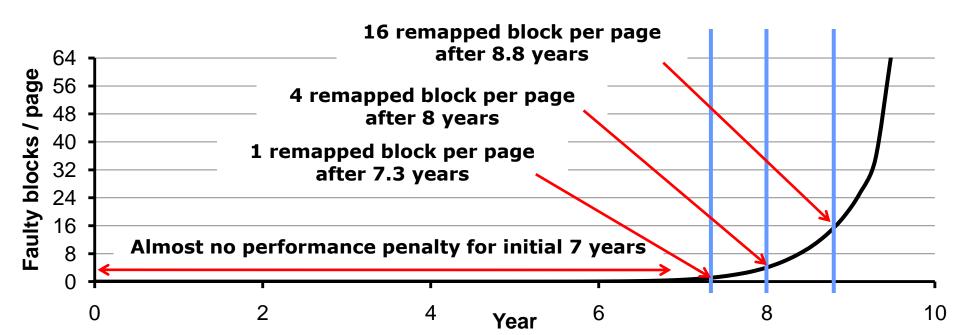


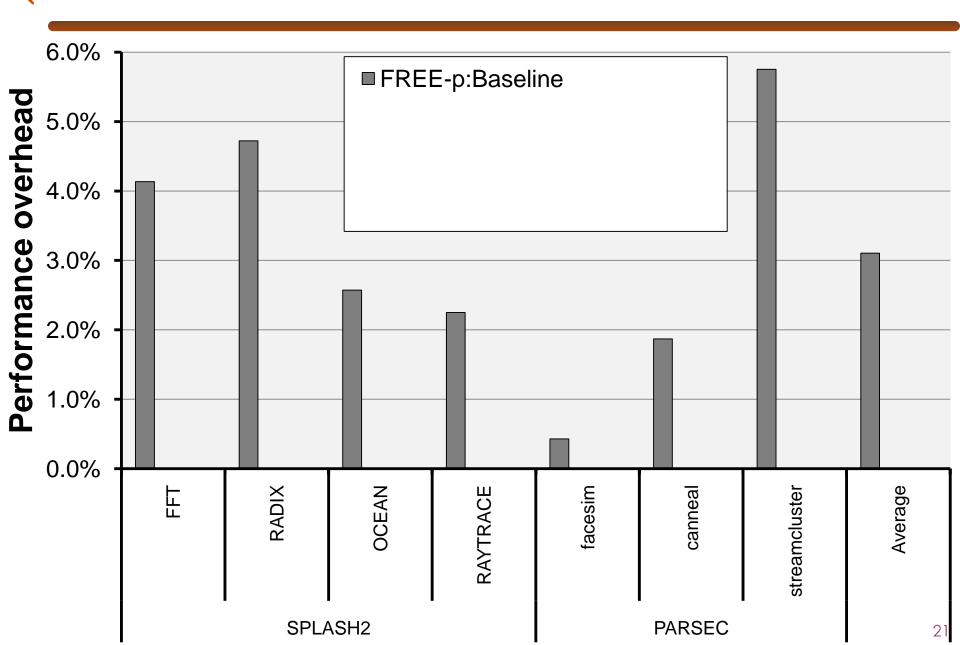
Capacity vs. Lifetime

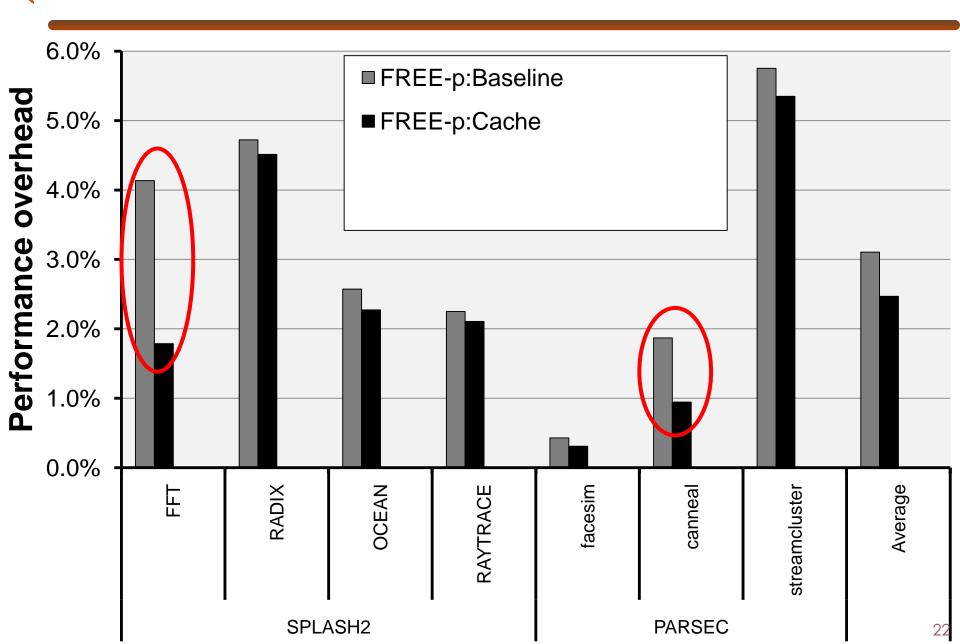


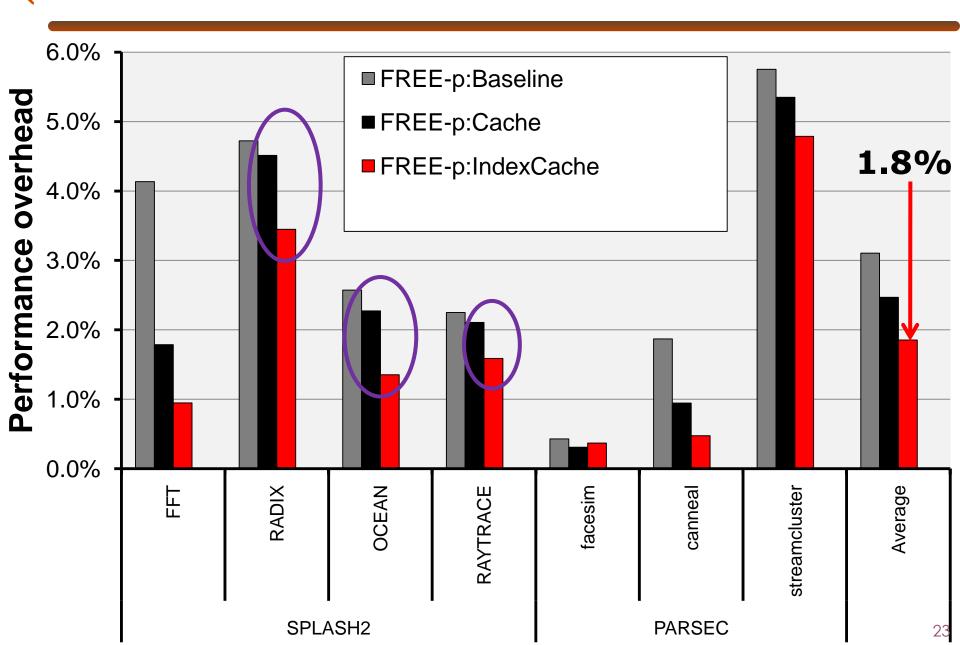
Performance Evaluation

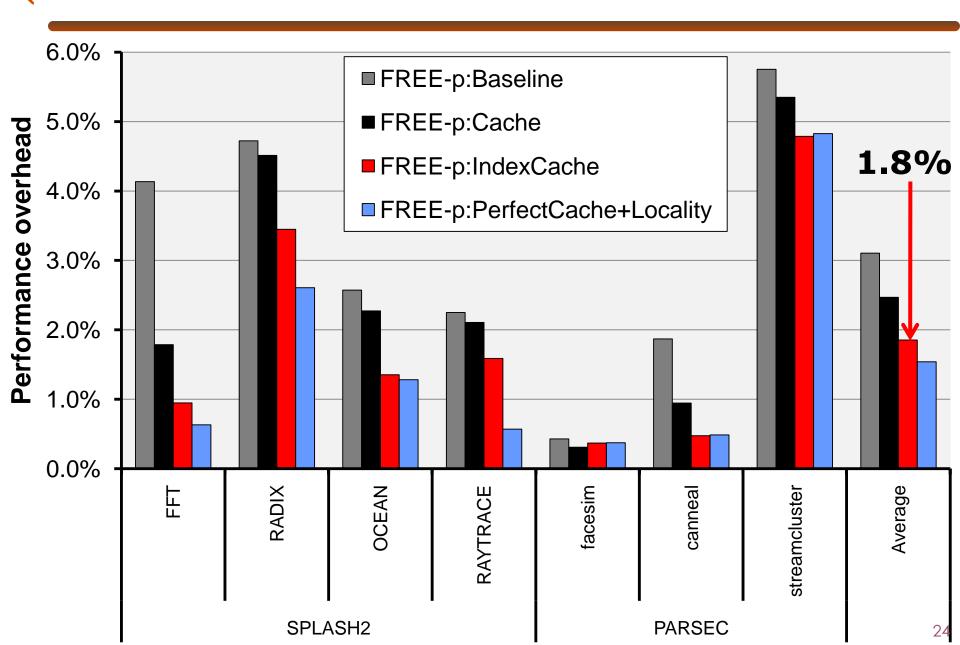
- In-order core with detailed NVRAM model
 - PCRAM with DDR3-like channel interface
- Performance depends on NVRAM wear-out status
 - Fault injection based on failure simulation











Performance Impact (Cont'd)

- After 8 years
 - Index Cache: 3.5~6.7% penalty
- After 8.8 years
 - Simple caching doesn't work any more
 - > 30% penalty
 - Index Cache: 10.7~13% penalty



Conclusions

FREE-p combines FR and multi-tiered ECC

- Protect against both Hard AND Soft errors
- 11.5% longer lifetime over ECP6
- Less than 2% performance degradation, even at 7 years
- 12.5% storage overhead (same as current DRAM protection)

Everything is implemented at the memory controller

- End-to-end protection
 - Hard and soft errors in the cell array
 - Errors on the periphery, wires, packaging, ...
- System designers determine protection level
 - Can be extended to chipkill-correct
- Simple and cheap (commodity) NVRAM devices



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